INFORMATION DISCLOSURE CITATION

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ATTY DOCKET NO.	SERIAL NO.
YOR920000173US2	Not Yet Assigned
Cohen et al.	
FILING: Concurrently Herewith	GROUP: Unknown

U.S. PATENT DOCUMENTS

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		6,143,582	11/07/2000	Vu et al.			
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			"Self-Aligned (Top and Bottom) Double-Gate MOSFET with a 25 nm Thick Silicon Channel", Hon-Sum Philip Wong, Kevin K. Chan, and Yuan Taur, IBM Thomas J. Watson Research Center, Yorktown Heights, NY, IEEE 1997, pp. 427-430
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Samuel A. Dr	11/29/03

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